

SHINDENGEN

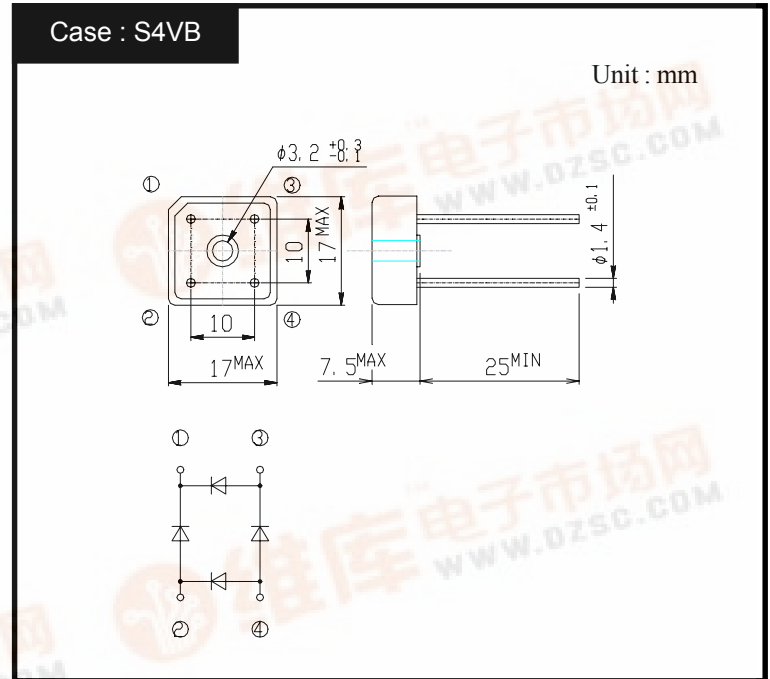
Bridge Diode

Square In-line Package

S4VB60

600V 4A

OUTLINE DIMENSIONS



RATINGS

● Absolute Maximum Ratings

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T _{stg}		-40~150	°C
Operating Junction Temperature	T _j		150	°C
Maximum Reverse Voltage	V _{RM}		600	V
Average Rectified Forward Current	I _O	50Hz sine wave, R-load, Ta=40°C With heatsink θ _{fa} =10°C/W	4	A
		50Hz sine wave, R-load, Ta=40°C Without heatsink	2.6	
Peak Surge Forward Current	I _{FSM}	50Hz sine wave, Non-repetitive 1cycle peak value, T _j =25°C	80	A
Current Squared Time	I ² t	1ms ≤ t < 10ms T _c =25°C	32	A ² s
Mounting Torque	TOR	(Recommended torque : 0.5N·m)	0.8	N·m

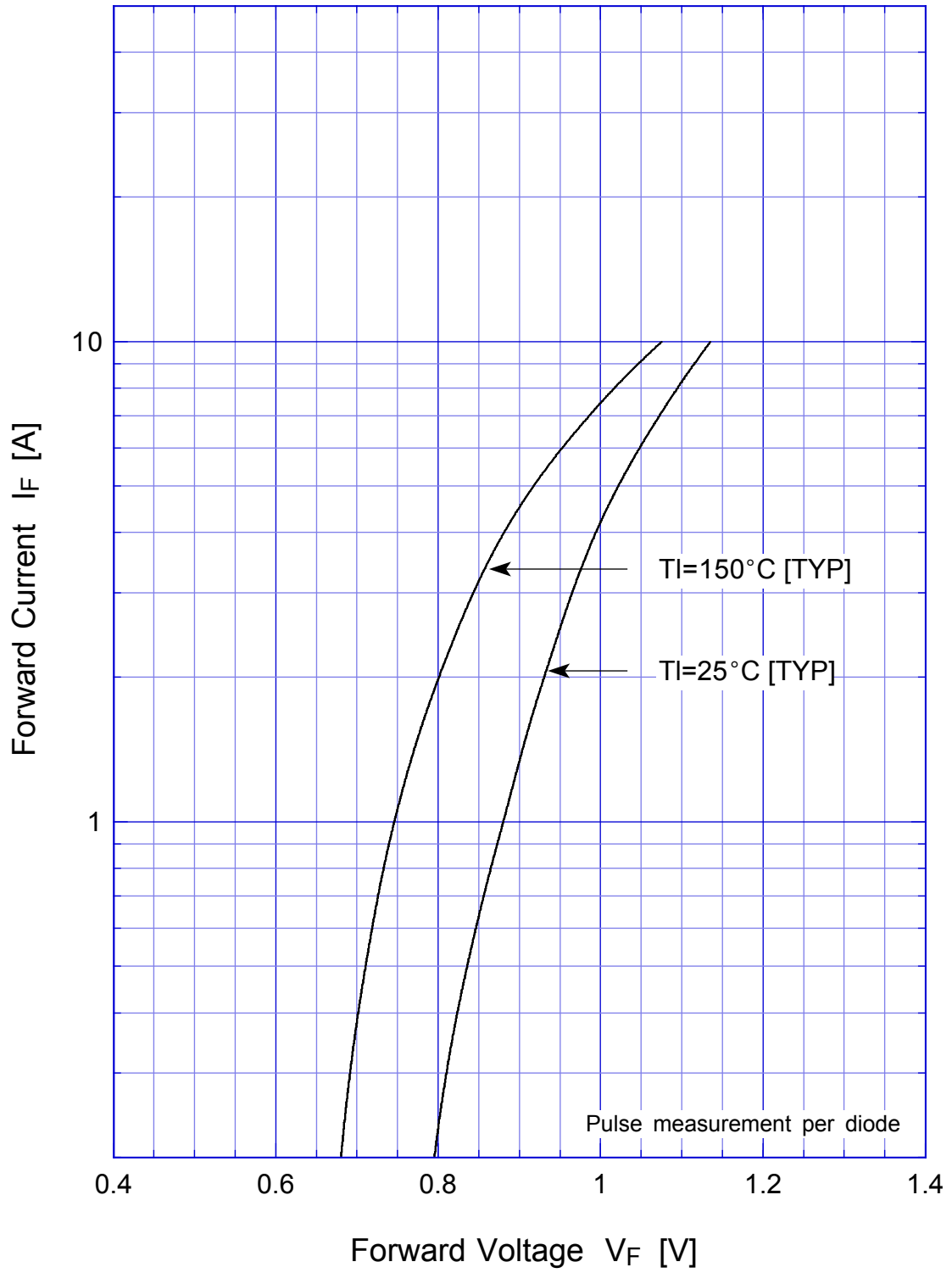
● Electrical Characteristics (T_i=25°C)

Item	Symbol	Conditions	Ratings	Unit
Forward Voltage	V _F	I _F =2A, Pulse measurement, Rating of per diode	Max.1.05	V
Reverse Current	I _R	V _R =V _{RM} , Pulse measurement, Rating of per diode	Max.10	μA
Thermal Resistance	θ _{jl}	junction to lead	Max.4.5	°C/W



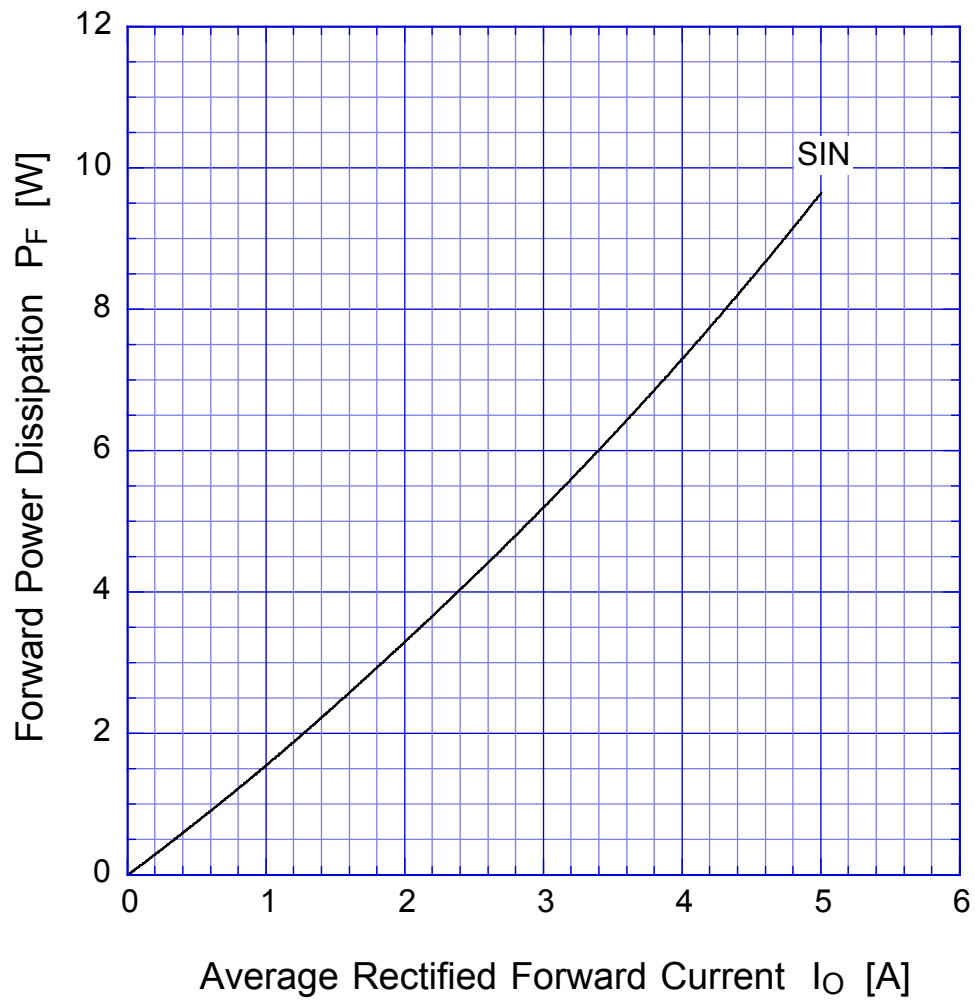
S4VBx

Forward Voltage



S4VBx

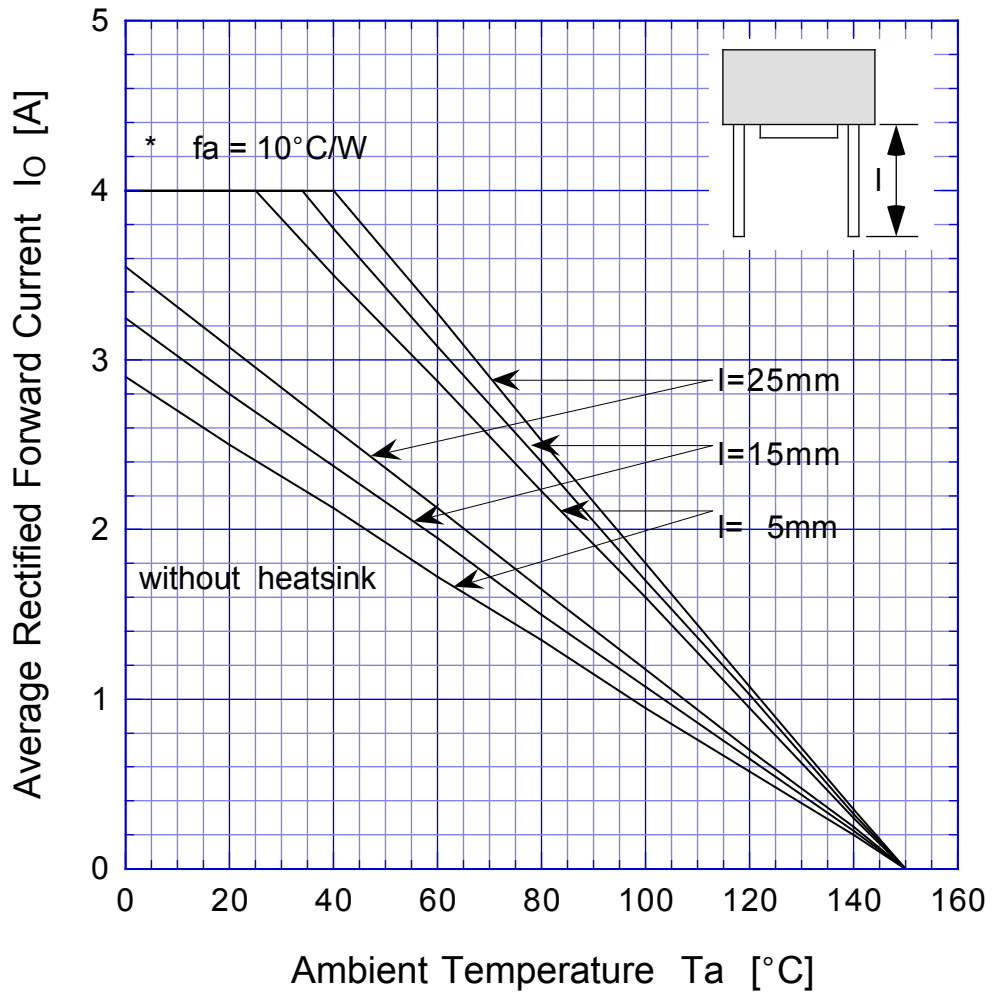
Forward Power Dissipation



$T_j = 150^\circ\text{C}$
Sine wave

S4VBx

Derating Curve



Sine wave

R-load

Free in air

* with thermal compound, TOR=3kg-cm

S4VBx

Peak Surge Forward Capability

